

FM6L52020L

Silicon N-channel MOSFET(FET) Silicon epitaxial planar type(SBD)

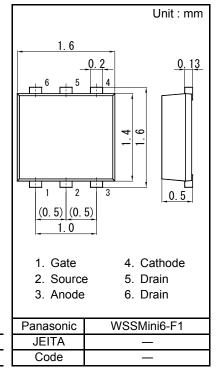
For switching For DC-DC Converter

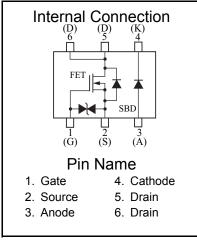
Features

- Low drain-source ON resistance : RDS (on) typ. = 80 m Ω (VGS = 4.0 V)
- Low drive voltage : 1.8 V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol : Y6

Packaging

Embossed type (Thermo-compression sealing) 10 000 pcs / reel (standard)





■ Absolute Maximum Ratings Ta = 25 °C

項目		Symbol	Rating	Unit			
FET	Drain to Source Voltage	VDS	20	V			
	Gate to Source Voltage	VGS	±10	V			
	Drain current	ID	2.2	Α			
	Peak drain current	IDp	8.0	Α			
	Channel temperature	Tch	150	°C			
SBD	Reverse voltage	VR	20	V			
	Forward current (Average)	IF(AV)	800	mA			
	Junction temperature	Tj	125	°C			
Overall	Total power dissipation *1	PD	540	mW			
	Operating ambient temperature	Topr	-40 to +85	°C			
	Storage temperature	Tstg	-55 to +125	°C			
Note	Note) *1 Measuring on ceramic substrate at 40 mm × 38 mm × 0.2 mm						

PD absolute maximum rating without a heat shink: 150 mW



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■ Electrical Characteristics Ta = 25 °C ± 3 °C

FET (N-ch.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Drain-source surrender voltage	VDSS	ID = 1.0 mA, VGS = 0	20			V	
Drain-source cutoff current	IDSS	VDS = 20 V, VGS = 0			1.0	μA	
Gate-source cutoff current	IGSS	VGS = ±8 V, VDS = 0			±10	μA	
Gate threshold voltage	VTH	ID = 1.0 mA, VDS = 10 V	0.4	0.85	1.3	V	
Drain-source ON resistance ^{*1}	RDS(on)1	ID = 1.0 A, VGS = 4.0 V		80	105	mΩ	
Drain-source ON resistance	RDS(on)2	ID = 0.5 A, VGS = 2.5 V		100	150		
Forward transfer admittance *1	Yfs	ID = 1.0 A, VDS = 10 V, f = 1 kHz	3.0			S	
Short-circuit input capacitance (Common source)	Ciss			280			
Short-circuit output capacitance (Common source)	Coss			18		pF	
Reverse transfer capacitance (Common source)	Crss			17			
Turn-on delay time ^{*2}	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		5		ns	
Rise time ^{*2}	tr	ID = 1.0 A		8		115	
Turn-off delay time *2	td(off)	VDD = 6 V, VGS = 4.0 to 0 V		20		ne	
Fall time ^{*2}	tf	ID = 1.0 A		18		ns	
Note) 1. Moscuring methods are based on IAPANESE INDUSTRIAL STANDARD, US C 7030 Measuring methods for transistors							

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors. 2. *1 Pulse measurement

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

SBD

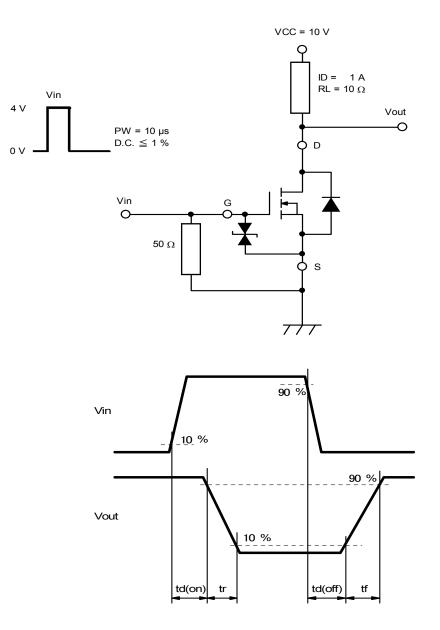
380								
Parameter	Symbol	Conditions	Min	Тур	Max	Unit		
Forward voltage	VF	IF = 800 mA			0.47	V		
Reverse current	IR	VR = 20 V			80	μA		

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

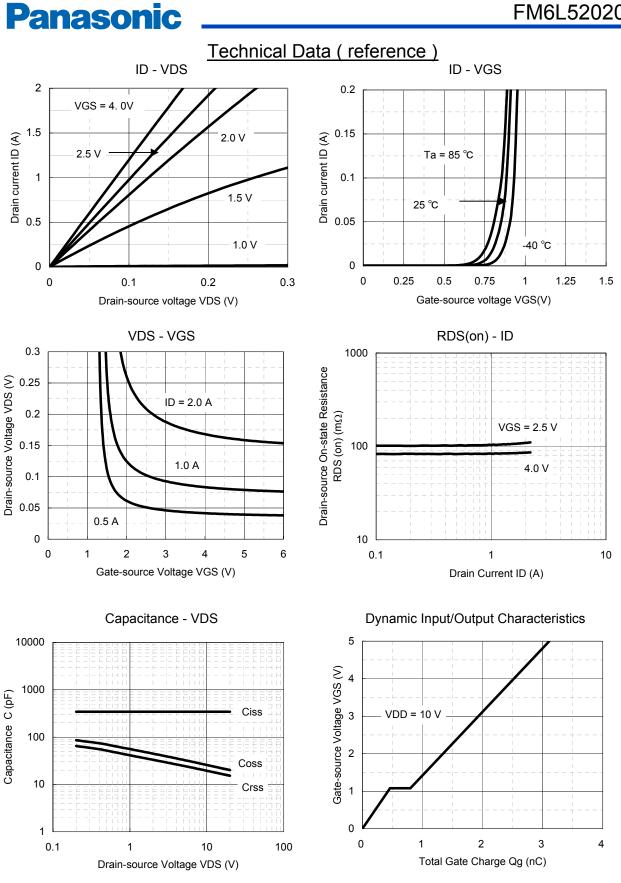
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*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

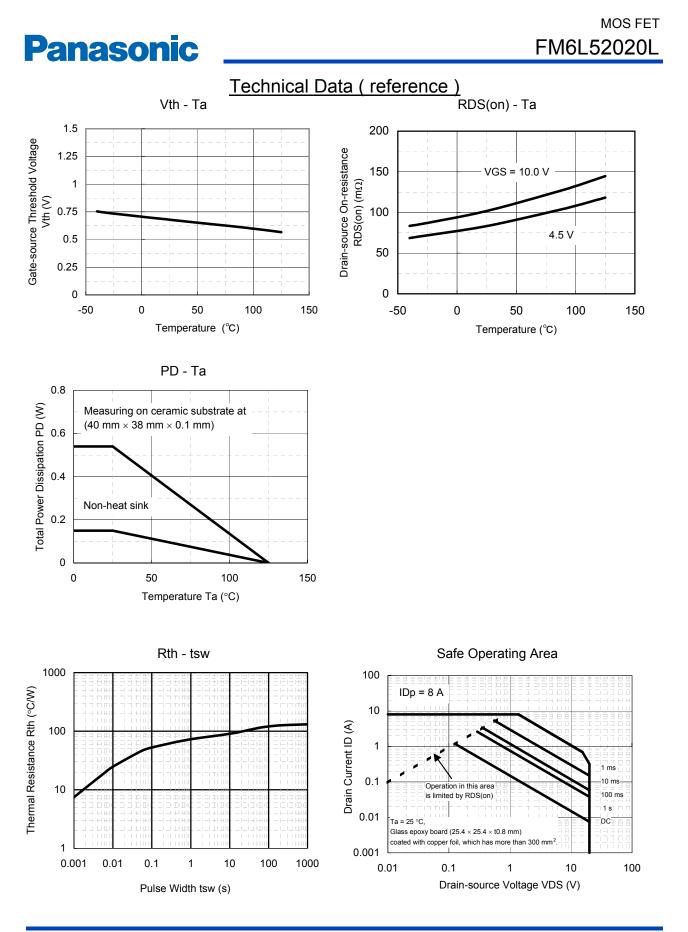




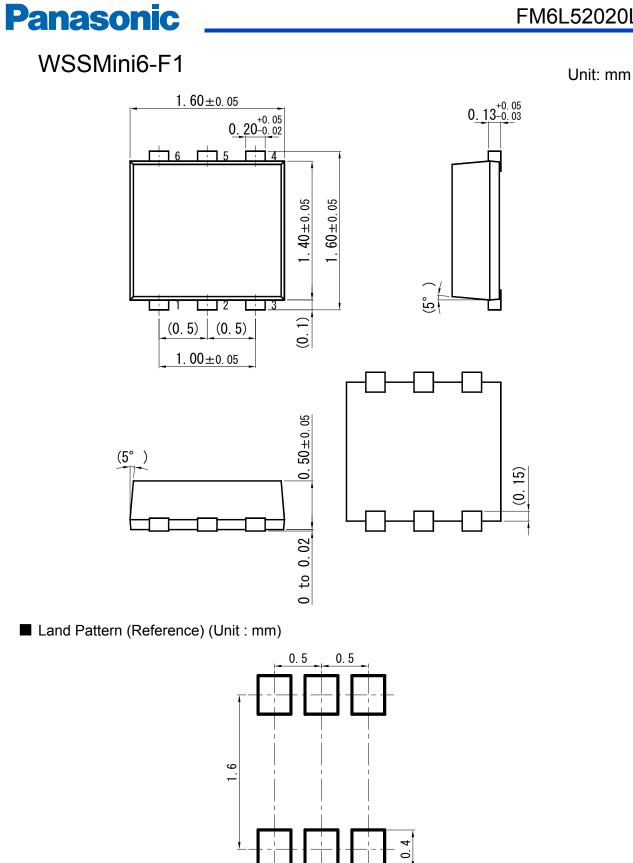




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